

## Joint Rewriting and Error Correction in Flash Memories

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#### Memory The Problem of Block Erasure

- Erasing a cell requires block erasure
  - Block erasure slows down programming
  - Degrades flash cells
- Solutions
  - Flash translation layer (FTL)
  - Coding for rewriting data
    - Floating codes
    - Buffer codes
    - Rank modulation codes
    - Write-once memory (WOM) codes



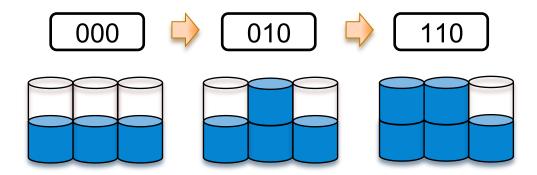
- Store data by programming cells which have been programmed before without erasing a cell.
- Constraint: a cell previously at level 1 (high threshold voltage) has to stay at level 1 after rewriting.
  - e.g. 101 -> 111
- After rewriting, the data stored by the previous writes no longer need to be recovered.

# Flash Memory The first write-once memory (WOM) code

**R. L. Rivest and A. Shamir**, "How to reuse a 'Write-Once' memory," Information and Control, vol. 55, pp. 1–19, 1982 (also published in STOC)

Data	Codeword (1 <sup>st</sup> write)	Codeword (2 <sup>nd</sup> write	<b>(</b> )
00	000	111	Write 2 bits
01	001	110	twice using 3 cells
10	010	101	Rate = 4/3 =
11	100	011	1.33 bits/cell

Example (with SLC): we first write data 10, then rewrite the data to 01.



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#### Capacities have been derived

[1] **C. Heegard**, "On the capacity of permanent memory", IEEE Transactions on Information theory, vol. 31, no. 1, 1985

Different WOM codes have been proposed.

Capacity-achieving codes have been proposed

- [1] A. Shipilka, "Capacity achieving multiwrite WOM codes", 2012.
- [2] D. Burshtein and A. Strugatski, "Polar write-once memory codes," ISIT 2012.

However, WOM codes for noisy channels are limited.

- [3] **G. Zemor and G. D. Cohen**, "Error-Correcting WOM-Codes", IEEE Transactions on Information Theory, vol. 37, no. 3, pp. 730-734, 1991.
- [4] E. Yaakobi, P. Siegel, A. Vardy, and J. Wolf, "Multiple Error-Correcting WOM-Codes", in IEEE Transactions on Information Theory, vol. 58, no. 4, pp. 2220-2230, 2012.

We study WOM codes which correct many errors.

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- Views a write as the decoding of a polar code:
  - Views the cells' state before the write as a noisy Polar codeword.
  - Views the cells' state after the write as the corrected (i.e., error-free) Polar codeword.
- More precisely, write/rewrite can be considered as lossy data compression.

[1] D. Burshtein and A. Strugatski, "Polar write-once memory codes," ISIT 2012.



## The Channel for Rewriting

- Smart idea by Burshtein and Strugatski:
  - Add dither to cell levels:
    - Let  $s \in \{0,1\}$  be the level of a cell.

v'

- Let  $g \in \{0,1\}$  be a pseudo-random number known to the WOM encoder and the WOM decoder.
- Let  $v=s\oplus g$  be called the value of the cell.
- Build a test channel for the write, which we shall call the WOM channel



 $0 \circ (1, 0)$   $1 - \alpha$   $0 \circ (0, 0)$   $0 \circ (s, v)$   $1 \circ (0, 1)$   $1 - \alpha$   $0 \circ (1, 1)$ 

a: fraction of the cells at "0" ε: fraction of the cells you can

program

Cell states and values

before rewrite



#### **WOM** codes

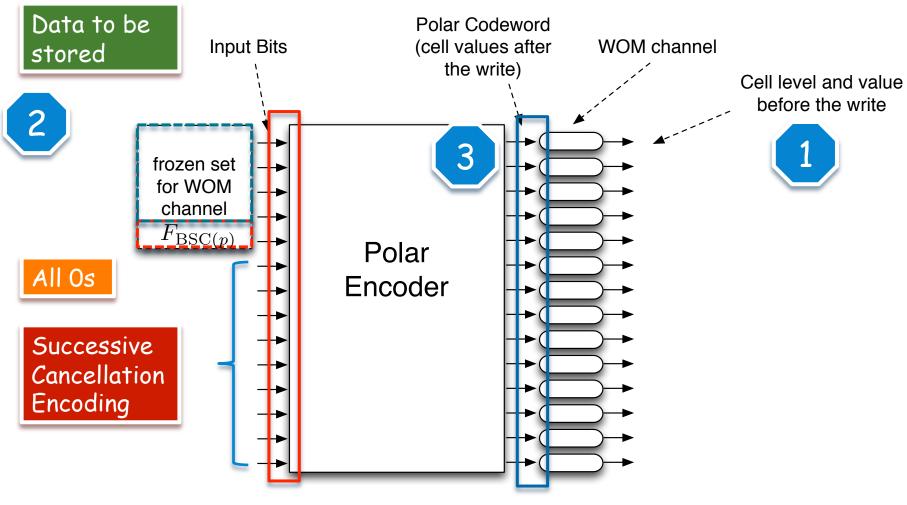




- We would like to construct a nested code.
  - A WOM codeword is also a channel codeword
- Consider two channels
  - WOM channel. Let its frozen set be  $F_{\mathrm{WOM}(\alpha,\epsilon)}$
  - BSC/noise channel. Let its frozen set be  $F_{\mathrm{BSC}(p)}$
- A codeword of polar codes for WOM channel is also a codeword of the codes for BSC channel under the condition

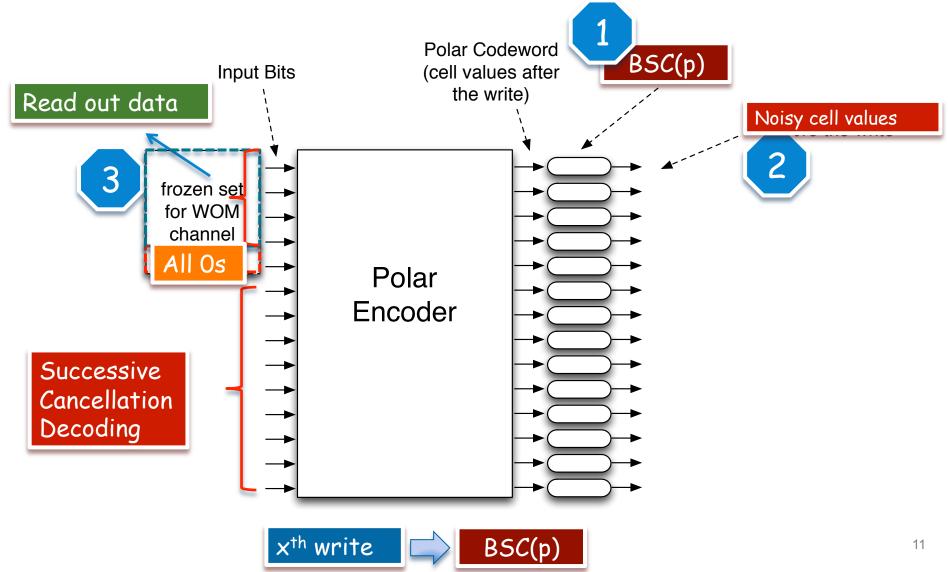
$$F_{\mathrm{BSC}(p)} \subseteq F_{\mathrm{WOM}(\alpha,\epsilon)}$$





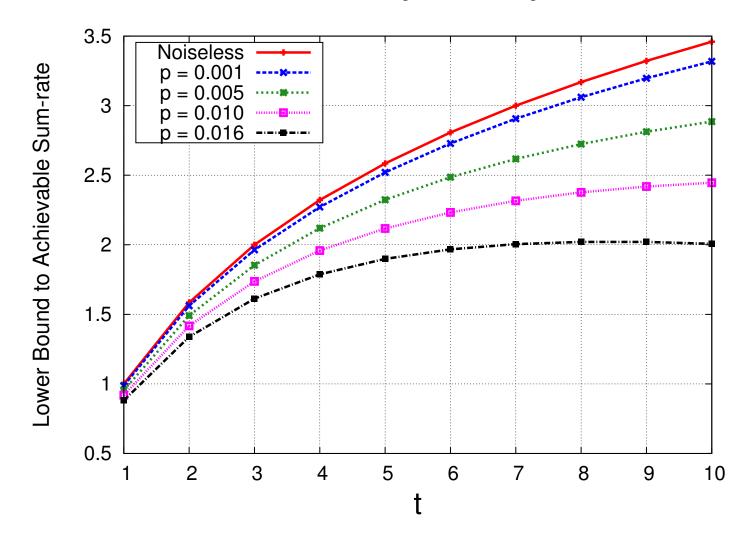


# Flash Memory The Decoding Scheme



### **Shipmemory** Lower Bounds to Achievable Sum-Rates

Sum-rate: total number of bits that can be stored using one cell through t writes.





- We proposed a coding scheme
  - allows multiple rewrites in one P/E cycle.
  - corrects a significant number of errors
  - Uses polar lossy source coding and channel coding

A. Jiang, Y. Li, E. En Gad, M. Langberg and J. Bruck. Joint Rewriting and Error Correction in Write-Once Memories. ISIT 2013.



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